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portion thereof to open or spread upward, said small-diameter contact hole being completely filled with a plug of a refractory conductive material, and said large-diameter contact hole being partly filled by said refractory conductive material which covers a sidewall surface of said large-diameter contact hole excluding said funnel-shaped portion, to a position which is lower than a lower end of said funnel-shaped portion by a predetermined distance, a wiring conductor layer being deposited on said insulator film to cover a top surface of said plug of said refractory conductive material and to fill at least in part space remaining in said large-diameter contact hole thereby to cover a bottom of said large-diameter contact hole and a surface of said sidewall of said refractory conductive material within said large-diameter contact hole, and to cover a surface of said funnel-shaped portion of said large-diameter contact hole.

12. A semiconductor device claimed in Claim 11, wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a refractory metal.

13. A semiconductor device claimed in Claim 11, wherein said large-diameter contact hole has an aspect ratio of not greater than 2, and said small-diameter contact hole has an aspect ratio of greater than 2.

14. A semiconductor device claimed in Claim 13, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

15. A semiconductor device claimed in Claim 11, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

16. A semiconductor device claimed in Claim 11, wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a refractory metal.

17. A semiconductor device claimed in Claim 16, wherein said large-diameter contact hole has an aspect ratio of not greater than 2, and said small-diameter contact hole has an aspect ratio of greater than 2.

18. A semiconductor device claimed in Claim 17, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

19. A semiconductor device claimed in Claim 16, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

20. A semiconductor device including both a large-diameter contact hole and a small-diameter contact hole formed to penetrate through an insulator film formed on a conductive portion to reach said conductive portion, each of said large-diameter contact hole and said small-diameter contact hole having a funnel-shaped portion formed on an upper portion thereof to open or spread upward, said small-diameter contact hole being completely filled with a plug of a refractory conductive

material, and said large-diameter contact hole being partly filled by said refractory conductive material which covers a sidewall surface of said large-diameter contact hole excluding said funnel-shaped portion; to a position which is lower than a lower end of said funnel-shaped portion by a predetermined distance, said refractory conductive material covering said sidewall surface of said large-diameter contact hole having a thickness on a lower portion of said hole, equal to about half the diameter of the small-diameter contact hole, a wiring conductor layer being deposited on said insulator film to cover a top surface of said plug of said refractory conductive material and to fill at least in part space remaining in said large-diameter contact hole thereby to cover a bottom of said large-diameter contact hole and a surface of said sidewall of said refractory conductive material within said large-diameter contact hole, and to cover a surface of said funnel-shaped portion of said large-diameter contact hole.

21. A semiconductor device claimed in Claim 20, wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a refractory metal.

22. A semiconductor device claimed in Claim 20, wherein said large-diameter contact hole has an aspect ratio of not greater than 2, and said small-diameter contact hole has an aspect ratio of greater than 2.

23. A semiconductor device claimed in Claim 22, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

24. A semiconductor device claimed in Claim 20, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

25. A semiconductor device claimed in Claim 20, wherein said refractory conductive material is a material selected from the group consisting of a refractory metal and a silicide of a refractory metal.

26. A semiconductor device claimed in Claim 25, wherein said large-diameter contact hole has an aspect ratio of not greater than 2, and said small-diameter contact hole has an aspect ratio of greater than 2.

27. A semiconductor device claimed in Claim 26, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

28. A semiconductor device claimed in Claim 25, wherein said predetermined distance is in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

REMARKS

Applicant has cancelled all of the presently pending claims. New claims 11-19 have been added to better encompass the full scope and breadth of the invention notwithstanding Applicant's belief that the present pending claims would have been allowable over the art. Accordingly, Applicant asserts that no claims have been added within the meaning of *Festo*. More particularly, independent claim 1 has been rewritten